

What is claimed is:

1. A dynamic burn-in method for a semiconductor device, comprising the steps of:

generating a determined signal;
5 increasing the frequency of the determined signal; and
providing the signal having the increased frequency to the semiconductor device.

2. A dynamic burn-in apparatus for a semiconductor device, comprising:

a signal generator; and
a frequency converter; wherein the frequency of the signal output from the signal generator is increased by the frequency converter, and the signal
15 having the increased frequency is provided to the semiconductor device.

3. A dynamic burn-in apparatus for a semiconductor device, wherein a signal output from a signal generator is provided to a semiconductor device to be tested in the burn-in tank, comprising:

a converter that is arranged at the output of the signal generator, wherein the frequency of the signal is increased by the converter and the signal output from the converter is provided to the
25 semiconductor device.

4. A dynamic burn-in apparatus of claim 3, wherein the semiconductor device is a general-purpose memory device, the converter comprises a synchronous oscillator and a waveform shaping circuit,
30 wherein the synchronous oscillator is synchronized with a clock output from the signal generator and generates a clock having higher frequency than that of the clock output from the signal generator, and the waveform shaping circuit shapes a control signal, a data signal
35 and an address signal that have the width corresponding the clock from a control signal, a data signal and an address signal output from the synchronous oscillator,

wherein the clock output from the synchronous oscillator and the control signal, the data signal and the address signal output from the waveform shaping circuit are provided to the semiconductor device.